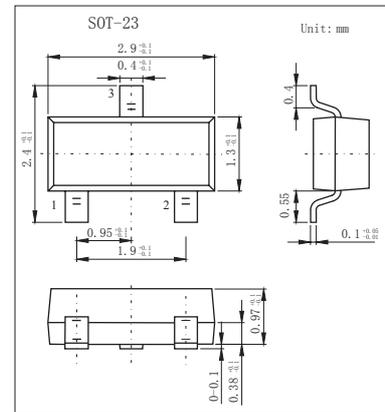
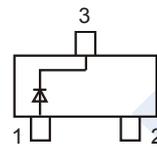


## Schottky Diodes

## 1SS349

## ■ Features

- Small package
- Low forward voltage:  $V_{F3} = 0.49V$ (Typ).
- Low voltage current:  $I_R = 50 \mu A$ (Max).

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Maximum(Peak) Reverse Voltage	$V_{RM}$	25	V
Reverse Voltage	$V_R$	20	V
Average Rectified Forward Current	$I_o$	1000	mA
Maximum(Peak) Forward Current	$I_{FM}$	3000	mA
Power Dissipation	$P$	200	mW
Junction Temperature	$T_j$	125	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55 to +125	$^\circ C$
Operating Poerating Temperature Range	$T_{opr}$	-40 to +100	$^\circ C$

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_R$	$I_R = 100 \mu A$	20			V
Forward voltage	$V_{F1}$	$I_F = 100 mA$		0.34		
	$V_{F2}$	$I_F = 500 mA$		0.42		
	$V_{F3}$	$I_F = 1000 mA$		0.49	0.55	
Reverse voltage leakage current	$I_R$	$V_R = 20 V$			50	$\mu A$
Capacitance between terminals	$C_T$	$V_R = 0 V, f = 1 MHz$		250		pF

## ■ Marking

Marking	L9
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# Schottky Diodes

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■ Typical Characteristics

